FM30P25EQ/T

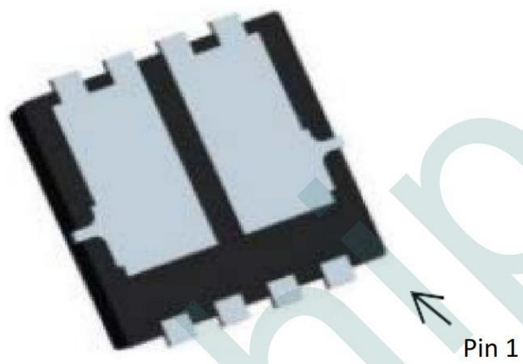
P-Channel Enhancement Mode MOSFET

- -30V, -25A
- $R_{DS(ON)}$=14mΩ @V_{GS} =-10V
- $R_{DS(ON)}$=18mΩ @ V_{GS}=-4.5V
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current

Application

- LCD TV
- Notebook
- Elevator
- Inductive heating Power tools
- Power tools

Package



PDFN3*3

Absolute Maximum Ratings (T_C=25℃unless otherwise specified)

Parameter		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	-30	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	（Tc=25℃）	I_D	-25	A
	（Tc=100℃）		-12	A
Pulsed Drain Current NOTE1		I_{DM}	80	A
Single Pulse Avalanche Energy NOTE2		E_{AS}	72	mJ
Power Dissipation	(Tc=25℃)	P_D	25	W
Thermal Resistance Junction-to-Case		$R_{\theta JC}$	0.2	℃/W
Operating and Storage Temperature Range		T_J , T_{STG}	-55 to +150	℃

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